

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the present application.

**Listing of Claims:**

**Claim 1 (currently amended):** For semiconductor manufacturing equipment,  
a ceramic susceptor comprising:

a ceramic substrate ~~deployed on~~ joined to a substantially ~~cylindrical~~ pipe-  
shaped shaft;

a resistive heating element formed either superficially or interiorly in said  
ceramic substrate; and

a concavity molded in a wafer-carrying face defined on a surface of said  
ceramic substrate through which said resistive heating element issues heat when the  
susceptor performs a heating operation, said concavity being 0.001 to 0.7 mm per  
300 mm length along the wafer-carrying face in negative arched contour when the  
susceptor is not heating; wherein

the pipe-shaped shaft is disposed to warp the substrate in a controlled  
manner, ~~so as to create at least a portion of~~ such that said concavity of the wafer-  
carrying face decreases upon heating of the substrate.

**Claim 2 (original):** A ceramic susceptor as set forth in claim 1, wherein the  
ceramic substrate is made of at least one ceramic selected from aluminum nitride,  
silicon nitride, aluminum oxynitride, and silicon carbide.

**Claim 3 (original):** A ceramic susceptor as set forth in claim 1, wherein the resistive heating element is made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

**Claim 4 (original):** A ceramic susceptor as set forth in claim 1, further comprising a plasma electrode disposed either in the surface or in the interior of said ceramic substrate.

**Claim 5 (original):** A ceramic susceptor as set forth in claim 2, wherein the resistive heating element is made from at least one metal selected from tungsten, molybdenum, platinum, palladium, silver, nickel, and chrome.

**Claim 6 (original):** A ceramic susceptor as set forth in claim 2, further comprising a plasma electrode disposed either in the surface or in the interior of said ceramic substrate.

**Claim 7 (original):** A ceramic susceptor as set forth in claim 3, further comprising a plasma electrode disposed either in the surface or in the interior of said ceramic substrate.

**Claim 8 (original):** A ceramic susceptor as set forth in claim 5, further comprising a plasma electrode disposed either in the surface or in the interior of said ceramic substrate.

**Claim 9 (currently amended):** A ceramic susceptor for semiconductor manufacturing equipment, the susceptor comprising:

a ceramic substrate ~~disposed on~~ joined to a substantially ~~cylindrical~~ pipe-shaped shaft and defining a wafer-carrying face;

a resistive heating element formed either superficially or interiorly in said ceramic substrate so as to issue heat through the wafer-carrying face when the susceptor is operated; and

an at-rest concavity configured in the wafer-carrying face of said ceramic substrate; wherein

the susceptor is formed so that the wafer-carrying face has a curvature of  $-0.001$  to  $0.7$  mm per 300 mm length when the susceptor is at rest, and so that when operated to heat said substrate to  $500^{\circ}\text{C}$ , the susceptor flexes such that the wafer-carrying face assumes a curvature of from  $-0.2$  mm to  $+0.45$  mm per 300 mm length.

**Claim 10 (previously presented):** The ceramic susceptor of claim 9 having an isothermal rating of less than 0.5 % at  $500^{\circ}\text{C}$ .